# imall

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## Contact us

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TSM650N15CS

UNIT

٧

mΩ

nC

Taiwan Semiconductor

VALUE

150

65

80

37

HALOGEN

**KEY PERFORMANCE PARAMETERS** 

 $V_{GS} = 10V$ 

 $V_{GS} = 6V$ 

PARAMETER

 $V_{DS}$ 

Qg

R<sub>DS(on)</sub>

(max)

### **N-Channel Power MOSFET**

 $150V, 9A, 65m\Omega$ 

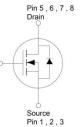
#### FEATURES

- Low R<sub>DS(ON)</sub> to minimize conductive losses
- Low gate charge for fast power switching
- 100% UIS and  $R_{q}$  tested
- Compliant to RoHS directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21

#### APPLICATIONS

- PoE
- LED Lighting
- Telecom Power





Note: MSL 1 (Moisture Sensitivity Level) per J-STD-020

PARAMETER   Drain-Source Voltage   Gate-Source Voltage		SYMBOL	LIMIT	UNIT V V	
		V <sub>DS</sub>	150		
		V <sub>GS</sub>	±20		
Continuous Drain Current (Note 1)	$T_{\rm C} = 25^{\circ}{\rm C}$		9	^	
	$T_A = 25^{\circ}C$	I <sub>D</sub>	4	A	
Pulsed Drain Current		I <sub>DM</sub>	36	А	
Single Pulse Avalanche Current (Note 2)		I <sub>AS</sub>	20	А	
Single Pulse Avalanche Energy (Note 2)		E <sub>AS</sub>	60	mJ	
Total Power Dissipation	$T_{\rm C} = 25^{\circ}{\rm C}$	P <sub>D</sub>	12.5	14/	
	T <sub>C</sub> = 125°C		2.5	W	
Total Power Dissipation	$T_A = 25^{\circ}C$	D	2.2	14/	
	T <sub>A</sub> = 125°C	P <sub>D</sub>	0.4	W	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	- 55 to +150	°C	

THERMAL PERFORMANCE					
PARAMETER	SYMBOL	LIMIT	UNIT		
Junction to Case Thermal Resistance	R <sub>eJC</sub>	10	°C/W		
Junction to Ambient Thermal Resistance	R <sub>⊖JA</sub>	57	°C/W		

**Thermal Performance Note:**  $R_{\Theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistances. The case-thermal reference is defined at the solder mounting surface of the drain pins.  $R_{\Theta JA}$  is guaranteed by design while  $R_{\Theta CA}$  is determined by the user's board design.

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PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250 \mu A$	$BV_{DSS}$	150			V
Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu A$	$V_{GS(TH)}$	2	2.7	4	V
Gate-Source Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA
Drain-Source Leakage Current	$V_{GS} = 0V, V_{DS} = 150V$	I <sub>DSS</sub>			1	μΑ
	$V_{GS} = 0V, V_{DS} = 150V$ T <sub>J</sub> = 125°C				100	
Drain-Source On-State Resistance (Note 3)	$V_{GS} = 10V, I_D = 4A$			51	65	mΩ
	$V_{GS} = 6V, I_D = 4A$	$R_{DS(on)}$		59	80	
Forward Transconductance (Note 3)	$V_{\text{DS}} = 5V, \ I_{\text{D}} = 4A$	<b>g</b> <sub>fs</sub>		11		S
Dynamic (Note 4)						
Total Gate Charge	$V_{GS} = 10V, V_{DS} = 75V,$ $I_D = 4A$	Qg		37		
Total Gate Charge	$V_{GS} = 6V, V_{DS} = 75V,$ $I_D = 4A$	Qg		24		nC
Gate-Source Charge		Q <sub>gs</sub>		9		
Gate-Drain Charge		Q <sub>gd</sub>		12		
Input Capacitance	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 75V f = 1.0MHz	C <sub>iss</sub>		1783		
Output Capacitance		C <sub>oss</sub>		94		pF
Reverse Transfer Capacitance		C <sub>rss</sub>		18		
Gate Resistance	f = 1.0MHz, open drain	R <sub>g</sub>	0.4	1.3	2.6	Ω
Switching (Note 4)						
Turn-On Delay Time		t <sub>d(on)</sub>		7		
Turn-On Rise Time	$V_{GS} = 10V, V_{DS} = 75V,$	t <sub>r</sub>		5		ns
Turn-Off Delay Time	$I_D = 4A, R_G = 2\Omega,$	t <sub>d(off)</sub>		17		
Turn-Off Fall Time		t <sub>f</sub>		11		
Source-Drain Diode				•		
Forward Voltage (Note 3)	$V_{GS} = 0V, I_{S} = 4A$	V <sub>SD</sub>			1	V
Reverse Recovery Time	$I_{S} = 4A$ ,	t <sub>rr</sub>		50		ns
Reverse Recovery Charge	dl/dt = 100A/µs	Q <sub>rr</sub>		97		nC

Notes:

1. Silicon limited current only.

L = 0.3mH,  $V_{GS}$  = 10V,  $V_{DD}$  = 50V,  $R_G$  = 25 $\Omega$ ,  $I_{AS}$  = 18A, Starting  $T_J$  = 25°C 2.

3. Pulse test: Pulse Width  $\leq$  300µs, duty cycle  $\leq$  2%.

4. Switching time is essentially independent of operating temperature.

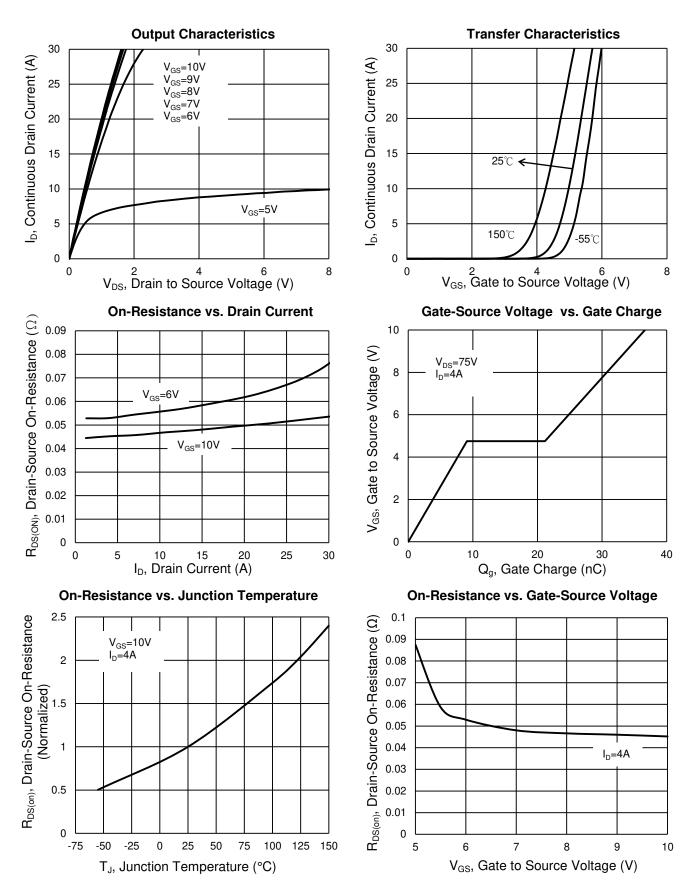
#### **ORDERING INFORMATION**

PART NO.	PACKAGE	PACKING		
TSM650N15CS RLG	SOP-8	2,500pcs / 13" Reel		



#### **CHARACTERISTICS CURVES**

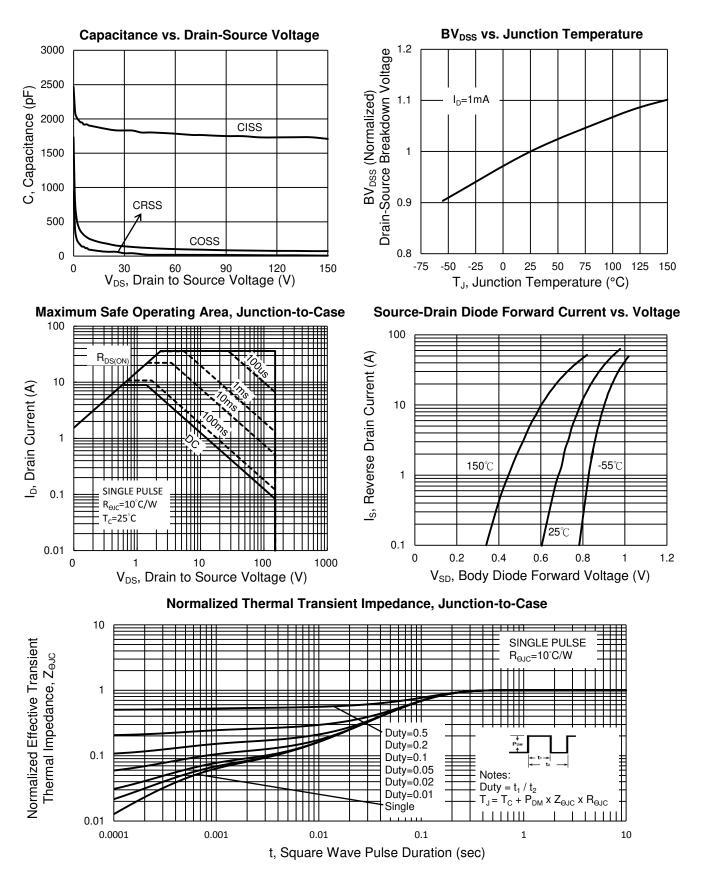
 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 





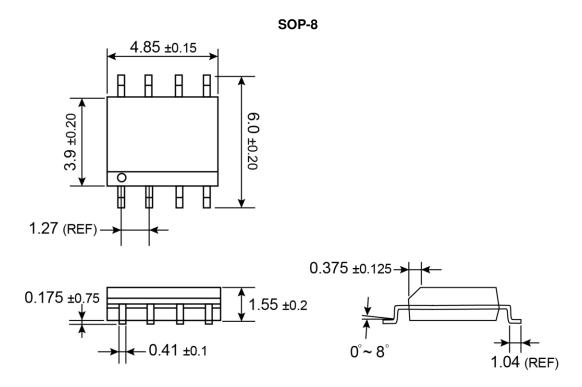
#### **CHARACTERISTICS CURVES**

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 

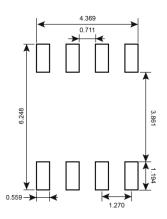




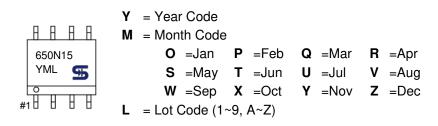
#### PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



#### SUGGESTED PAD LAYOUT (Unit: Millimeters)



#### **MARKING DIAGRAM**





### **TSM650N15CS**

Taiwan Semiconductor

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